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Customer Support Dept.
April 1, 2003



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Silicon NPN Epitaxial Planar



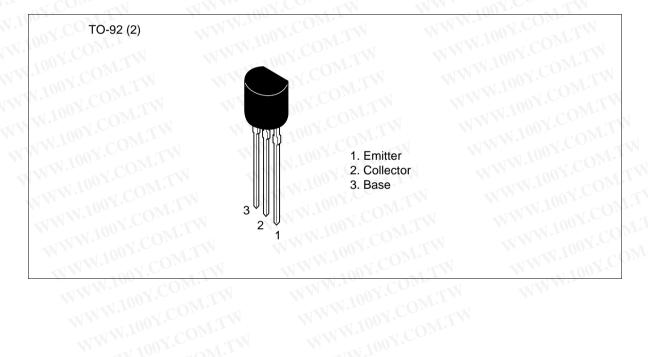
ADE-208-1046 (Z) 1st. Edition Mar. 2001

Application

- 2SC460 high frequency amplifier, mixer
- 2SC461 VHF amplifier, mixer

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Outline



Absolute Maximum Ratings (Ta = 25°C)

Item CON	Symbol	2SC460	2SC461	Unit
Collector to base voltage	V_{CBO}	30	30	V
Collector to emitter voltage	V_{ceo}	30	30	V
Emitter to base voltage	V _{EBO}	5 1001	5	V
Collector current	I_{c}	100	100	mA
Collector power dissipation	P _c	200	200	mW
Junction temperature	CONTINU	150	150	°C
Storage temperature	Tstg	-55 to +150	-55 to +150	√ °C
M.3	COM	MW.	ON COM	W

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Electrical Characteristics ($Ta = 25^{\circ}C$)

	Symbol	2SC460		2SC461					
Item		Min	Тур	Max	Min	Тур	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	30		_ <	30	N.100	7.C	VII	$I_{c} = 10 \ \mu A, I_{E} = 0$
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	30	TW	_	30	LIVE.	00¥.	V	$I_{c} = 1 \text{ mA}, R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	5	M.T.Y		5	MM.	1 0 07	V.CO	$I_E = 10 \mu A, I_C = 0$
Collector cutoff current	I _{CBO}	-TC	$M_{\cdot,r}$	0.5	_	JVV	0.5	μA	$V_{CB} = 18 \text{ V}, I_{E} = 0$
Emitter cutoff current	I _{EBO}) <u>F.</u>	07/1.	0.5	_		0.5	μΑ	$V_{EB} = 2 \text{ V}, I_{C} = 0$
Base to emitter voltage	V _{BE}	001.	0.63	0.75	_	0.63	0.75	V	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
DC current transfer ratio	h _{FE} *1	35	<u>-</u> 01	200	35	_//	200	100 1	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector to emitter saturation voltage	$V_{\text{CE(sat)}}$	1.100	0.6	1.1	N	0.6	1.1	, V 00	$I_{\rm C}$ = 10 mA, $I_{\rm B}$ = 1 mA
Gain bandwidth product	f _T	Min	230	$O_{\overline{M}^{I^{*}}}$,	T	230	WW	MHz	$V_{CE} = 12 \text{ V}, I_{C} = 2 \text{ mA}$
Collector output capacitance	C _{ob}	41.11	1.8	3.5	TW	1.8	3.5	pF	$V_{CB} = 10 \text{ V}, I_{E} = 0,$ f = 1 MHz
10.7 MHz power gain	PG N	26	29	V.CO	M-TV	\ <u>_</u>	-1/1	dB	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}$ f = 10.7 MHz
100 MHz power gain	PG	WW	V 10	ON.C	13	17	_	dB	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}$ f = 100 MHz
Noise figure	NF	M	2.0	100Y	COM	T.TW		dB	$V_{CE} = 6 \text{ V}, I_{E} = -1 \text{ mA}$ $f = 1 \text{MHz}$ $R_g = 500 \Omega$
Note: 1. The 2SC460	and 2SC4	l61 are	groupe	ed by h	e as fol	lows.	N	V	M.1003.
A B	C	4	NW						
35 to 70 60 to 120	100 to	200	WW						

Note: 1. The 2SC460 and 2SC461 are grouped by h_{FE} as follows. WWW.100Y.COM.TW

35 to 70 60 to 120 100 to 2

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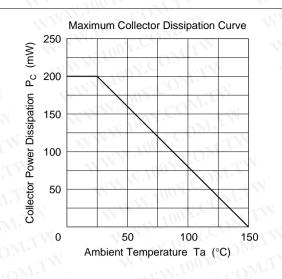
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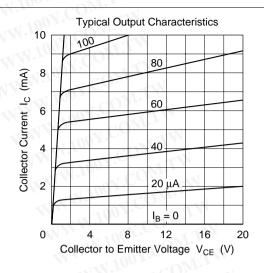
Small Signal y Parameters ($V_{CE} = 6 \text{ V}$, $I_{C} = 1 \text{ mA}$, Emitter Common)

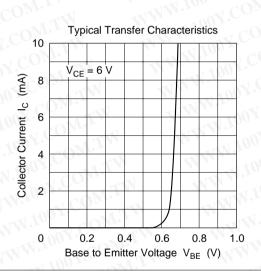
ltem	Symbol	f	2SC460A, 2S461A	2SC460B, 2SC461B	2SC460C, 2SC461C	Unit
Input admittance	yie	455 kHz	0.58 + j0.074	0.42 + j0.068	0.30 + j0.051	mS
		4.5 MHz	0.65 + j0.79	0.50 + j0.7	0.35 + j0.57	-
		10.7 MHz	0.91 + j2.0	0.61 + j1.9	0.39 + j1.3	=
		100 MHz	7.4 + j14	5.6 + j12	3.8 + j6.0	=
Reverse transfer admittance	yre	455 kHz	-j0.003	-j0.003	-j0.003	mS
		4.5 MHz	-j0.04	-j0.04	-j0.04	_
		10.7 MHz	−j0.13	-j0.13	-j0.13	=
		100 MHz	-j1.0	-j1.0	-j1.0	=
Forward transfer admittance	yfe	455 kHz	38 – j0.1	37 – j0.1	37 – j0.2	mS
		4.5 MHz	35 – j1.0	35 – j1.2	34 – j1.8	N
		10.7 MHz	34 – j2.5	34 – j2.5	33 – j4.5	W
		100 MHz	28 – j20	28 – j19	20 – j19	TW
Output admittance	yoe	455 kHz	0.0098 + j0.009	0.013 + j0.009	0.016 + j0.012	mS
		4.5 MHz	0.02 + j0.09	0.023 + j0.092	0.03 + j0.10	I'r
		10.7 MHz	0.11 + j0.4	0.11 + j0.4	0.12 + j0.4	$M_{*,T}$
		100 MHz	0.40 + j1.7	0.50 + j2.0	0.83 + j2.0	M.T

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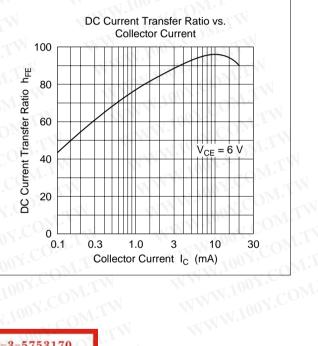
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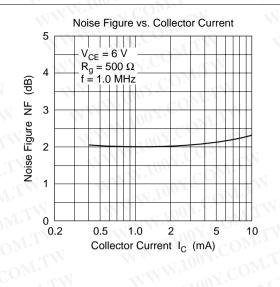


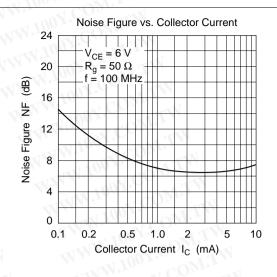


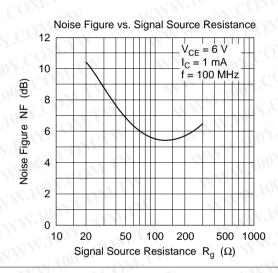


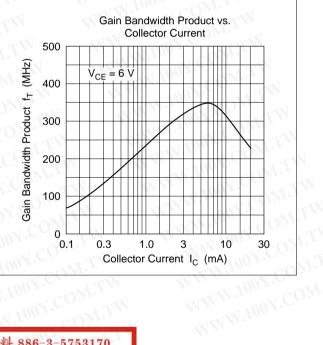
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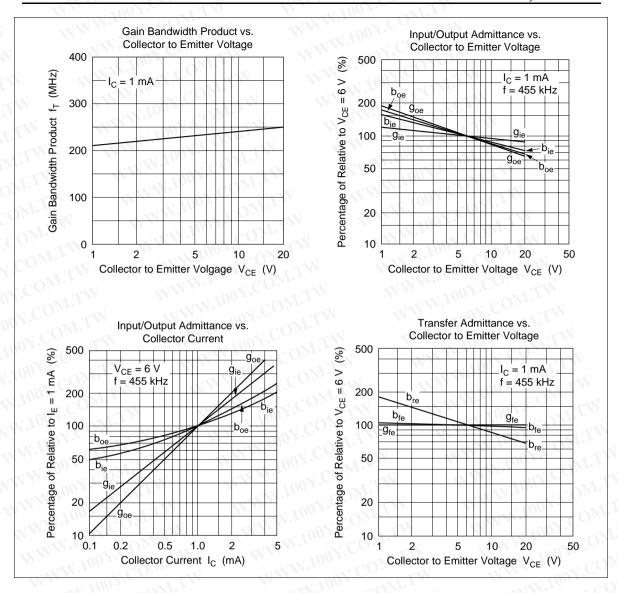


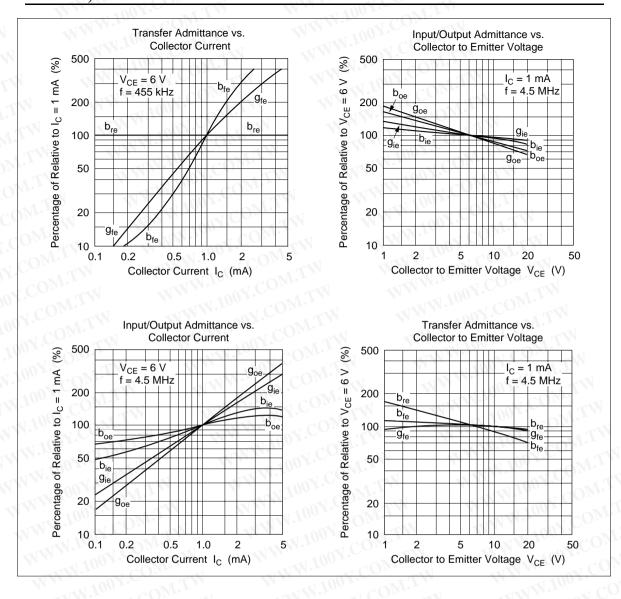




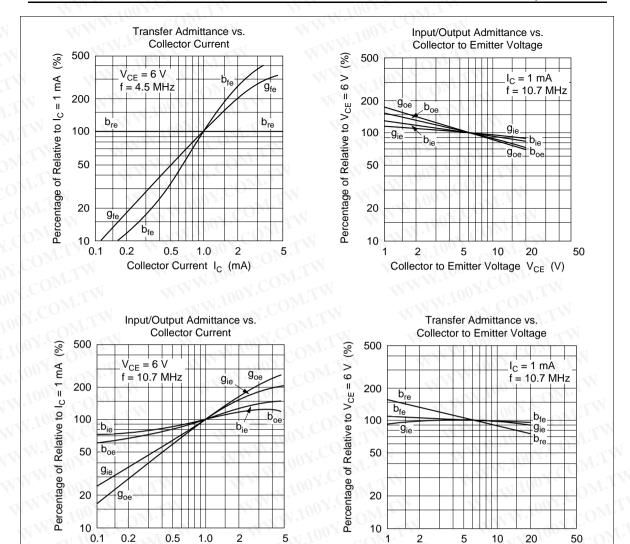








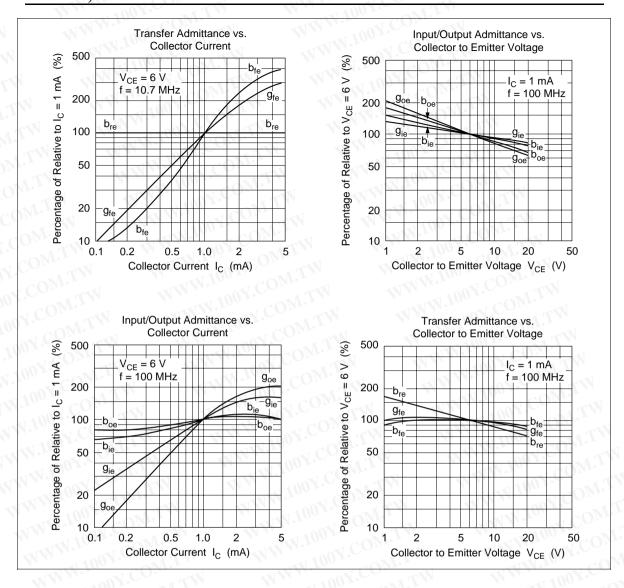
Collector to Emitter Voltage V_{CE} (V)

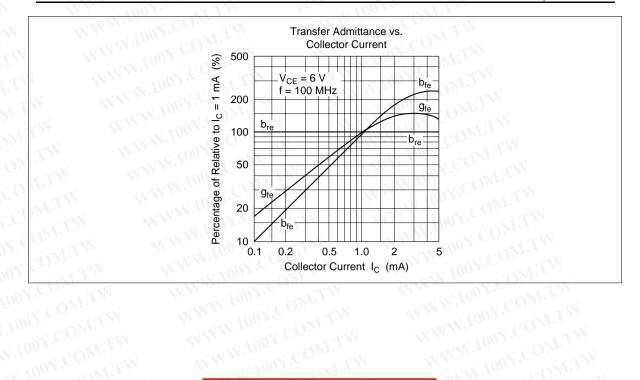


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Collector Current I_C (mA)

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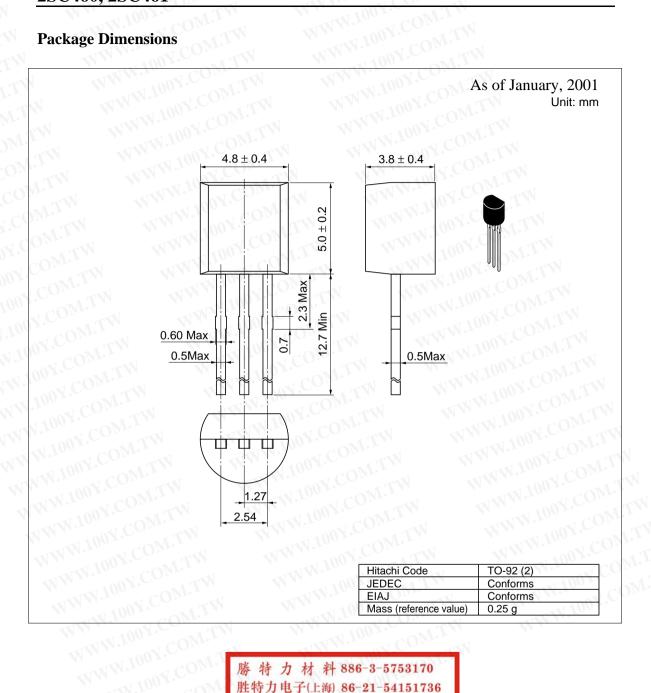
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Package Dimensions



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2SC460, 2SC461

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